

Supplementary Information

Role of solution-processed high- κ gate dielectrics in electrical performances of oxide thin-film transistors

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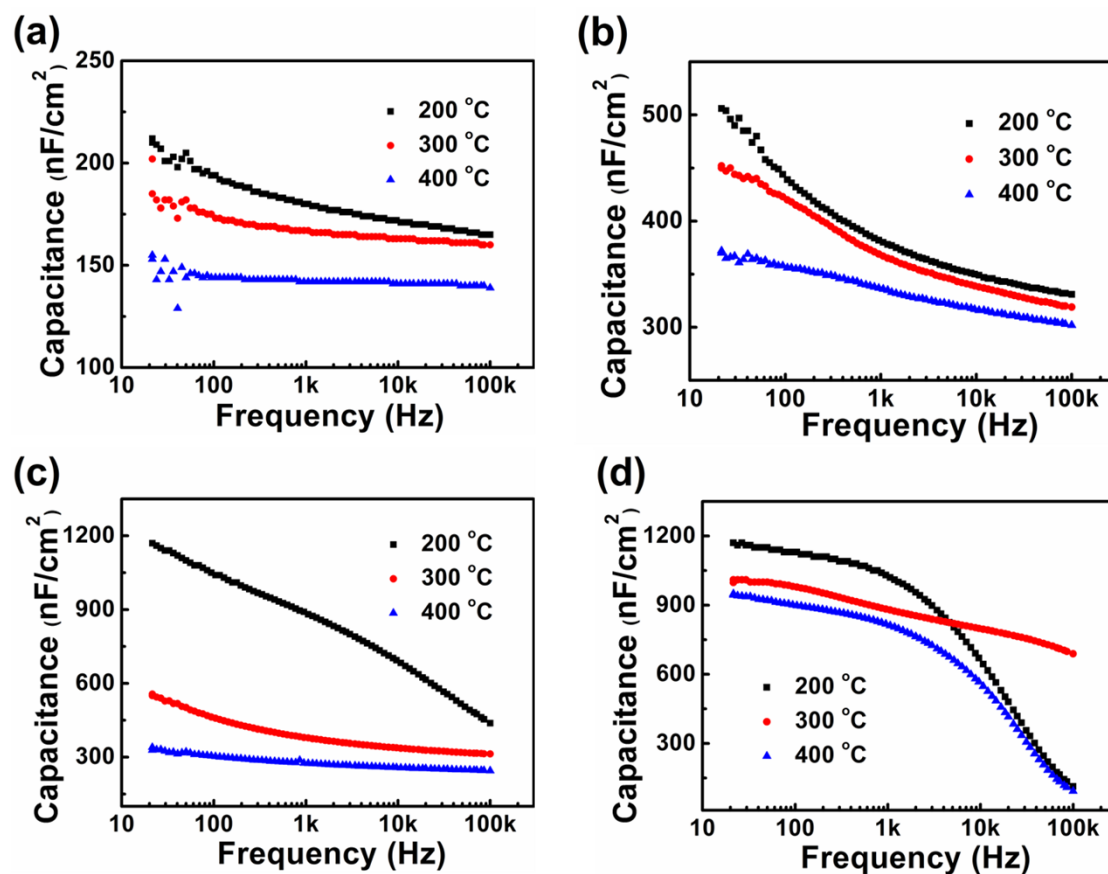


Figure S1. Capacitance vs. frequency plots for (a) AlO_x, (b) ZrO_x, (c) YO_x and (d) TiO_x dielectrics annealed at different temperatures.

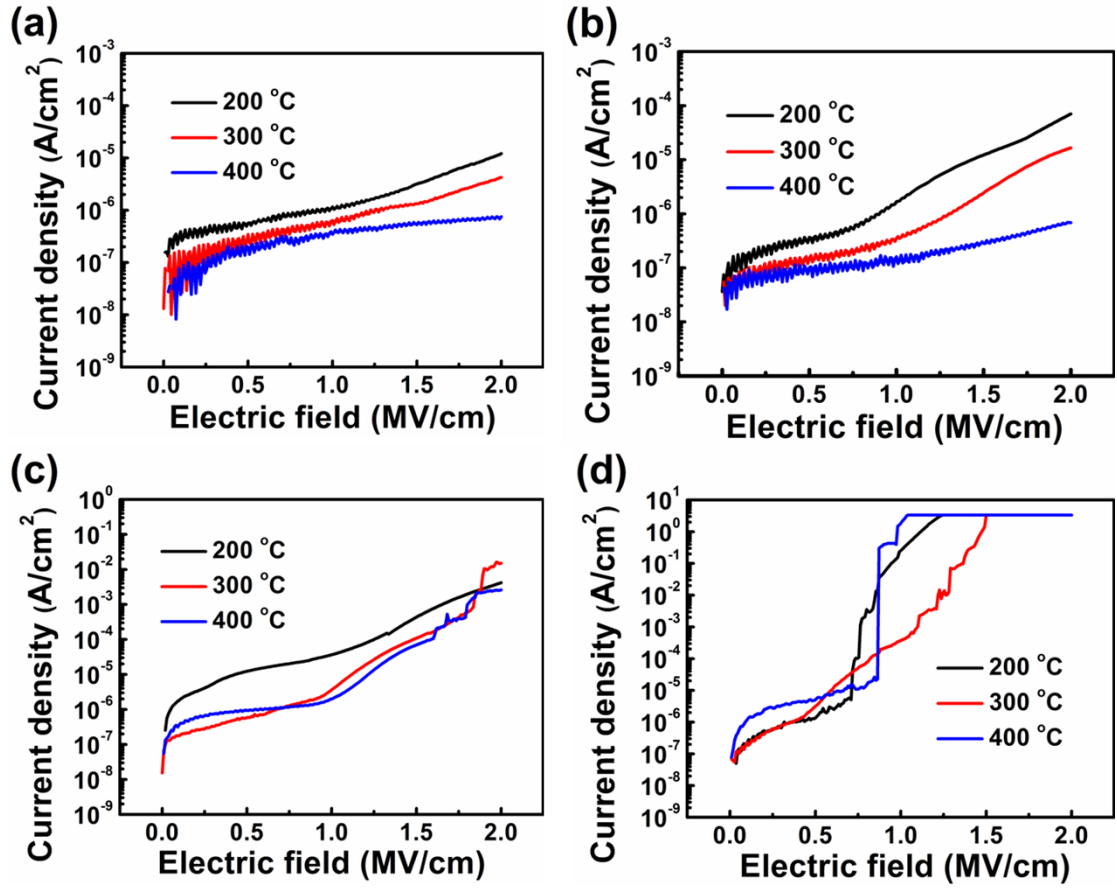


Figure S2. Leakage current density vs. electrical field plots for (a) AlO_x, (b) ZrO_x, (c) YO_x and (d) TiO_x dielectrics annealed at different temperatures.